

CNX35U CNX36U CNX38U CNX39U

DESCRIPTION

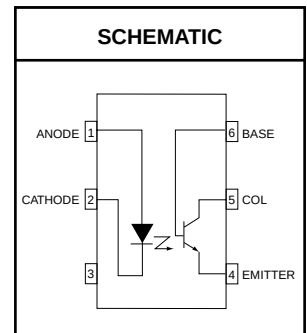
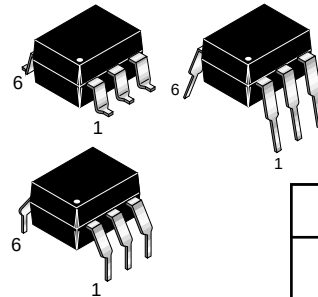
The CNX35U, CNX36U CNX38U and CNX39U are optically coupled isolators consisting of an infrared emitting GaAs diode and a silicon NPN phototransistor with accessible base. These devices are housed in 6-pin dual-in-line packages (DIP).

FEATURES

- High output/input DC current transfer ratio
- Low saturation voltage
- UL recognized (File # E90700)
- VDE recognized (File # 94766)
- Ordering option '300' (e.g. CNX35U.300)

APPLICATIONS

- Power supply regulators
- Digital logic inputs
- Microprocessor inputs
- Appliance sensor systems
- Industrial controls



Parameters	Symbol	Device	Value	Units
TOTAL DEVICE				
Storage Temperature	T _{STG}	All	-55 to +150	°C
Operating Temperature	T _{OPR}	All	-40 to +100	°C
Lead Solder Temperature	T _{SOL}	All	260 for 10 sec	°C
EMITTER				
Continuous Reverse Voltage	V _R	All	5	V
Continuous Forward Current	I _F	All	100	mA
Forward Current - Peak (10 μs pulse, δ = 0.01)	I _{F(pk)}	All	3.0	A
Total Power Dissipation up to 25°C Ambient Derate Linearly from 25°C	P _D	All	200	mW
		All	2.0	mW/°C
DETECTOR				
Collector to Emitter Voltage (open base)	V _{CEO}	CNX38U	80	V
		CNX35U, CNX36U, CNX39U	30	
Collector to Base Voltage (open emitter)	V _{CBO}	CNX38U	120	V
		CNX35U, CNX36U, CNX39U	70	
Emitter to Collector Voltage (open base)	V _{ECO}	All	7	V
DC Collector Current	I _C	All	100	mA
Detector Power Dissipation up to 25°C Ambient Derate Linearly from 25°C	P _D	All	200	mW
		All	2.0	mW/°C

CNX35U CNX36U CNX38U CNX39U

ELECTRICAL CHARACTERISTICS (T_A = 25°C Unless otherwise specified.)

INDIVIDUAL COMPONENT CHARACTERISTICS

Parameters	Test Conditions	Symbol	Device	Min	Typ	Max	Units
EMITTER							
Input Forward Voltage	I _F = 10 mA	V _F	All		1.15	1.5	V
Reverse Current	V _R = 5 V	I _R	All			10	μA
DETECTOR							
Leakage Current Collector to Emitter	V _{CE} = 10 V	I _{CEO}	CNX35U, CNX36U, CNX39U		2	50	nA
	V _{CE} = 50 V		CNX38U		2	50	nA
	V _{CE} = 10 V, T _A = 70°C		CNX35U, CNX36U, CNX39U			10	μA
	V _{CE} = 50 V, T _A = 70°C		CNX38U			10	μA
	V _{CE} = 10 V	I _{CBO}	All			20	nA
Breakdown Voltage							
Collector to Emitter	I _C = 1 mA, I _F = 0	BV _{CEO}	CNX35U, CNX36U, CNX39U	30			V
			CNX38U	80			
Collector to Base	I _C = 0.1 mA, I _F = 0	BV _{CBO}	CNX35U, CNX36U, CNX39U	70			V
			CNX38U	120			
Emitter to Collector	I _E = 0.1 mA, I _F = 0	BV _{ECO}	All	7			V

ISOLATION CHARACTERISTICS

Characteristic	Test Conditions	Symbol	Min	Typ	Max	Units
Input-Output Isolation Voltage	t = 1 min.	V _{ISO}	5,300			V _{RMS}
Isolation Resistance	V _{I-O} = 500 VDC	R _{ISO}	1	10		TΩ
Isolation Capacitance	I _F = 0, V = 0V, f = 1 MHz	C _{ISO}		0.6	1.3	pF

CNX35U CNX36U CNX38U CNX39U

TRANSFER CHARACTERISTICS (T _A = 25°C Unless otherwise specified.)							
DC Characteristics	Test Conditions	Symbol	Device	Min	Typ	Max	Units
Output/Input Current Transfer Ratio	I _F = 10 mA, V _{CE} = 0.4 V	CTR	CNX35U	40		160	%
			CNX39U	60		100	
			CNX36U	80		200	
	CNX38U		70		210		
			50				
	I _F = 10 mA, V _{CE} = 10 V		All	15			
I _F = 16 mA, V _{CE} = 0.4 V							
Collector-Emitter Saturation Voltage	I _F = 2 mA, V _{CE} = 5 V	V _{CE(SAT)}	CNX35U, CNX39U		0.15	0.4	V
	I _F = 10 mA, I _C = 2 mA		CNX36U		0.19	0.4	
	I _F = 10 mA, I _C = 4 mA		CNX38U		0.2	0.4	
	I _F = 16 mA, I _C = 2 mA						
AC Characteristics	Test Conditions	Symbol	Device	Min	Typ	Max	Units
Non-Saturated Switching Times							
Turn-On Time See Fig. 1 and Fig. 2	R _L = 100 Ω, I _C = 2 mA, V _{CC} = 5 V	t _{on}	CNX35U			20	μs
			CNX39U			20	
			CNX36U			20	
	R _L = 100 Ω, I _C = 4 mA, V _{CC} = 5 V		CNX38U			20	
Turn-Off Time See Fig. 1 and Fig. 2	R _L = 100 Ω, I _C = 2 mA, V _{CC} = 5 V	t _{off}	CNX35U			20	μs
			CNX39U			20	
			CNX36U			20	
	R _L = 100 Ω, I _C = 4 mA, V _{CC} = 5 V		CNX38U			20	
Saturated Switching Times							
Turn-On Time See Fig. 1 and Fig. 2	R _L = 1 kΩ, I _C = 2 mA, V _{CC} = 5 V	t _{on}	CNX35U			50	μs
			CNX39U			50	
			CNX36U			50	
	R _L = 1 kΩ, I _C = 4 mA, V _{CC} = 5 V		CNX38U			50	
Turn-Off Time See Fig. 1 and Fig. 2	R _L = 1 kΩ, I _C = 2 mA, V _{CC} = 5 V	t _{off}	CNX35U			50	μs
			CNX39U			50	
			CNX36U			50	
	R _L = 1 kΩ, I _C = 4 mA, V _{CC} = 5 V		CNX38U			50	

CNX35U CNX36U CNX38U CNX39U

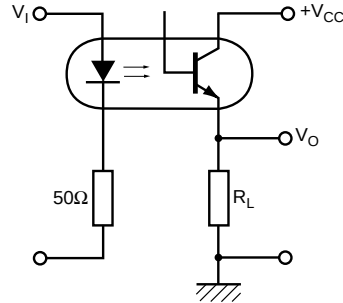


Fig. 1 Switching Test Circuit

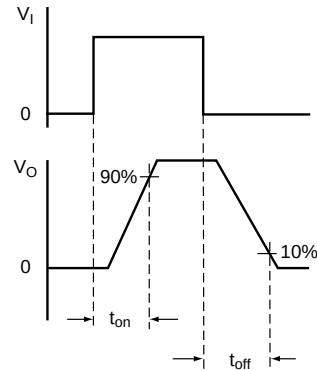


Fig. 2 Switching Test Waveforms

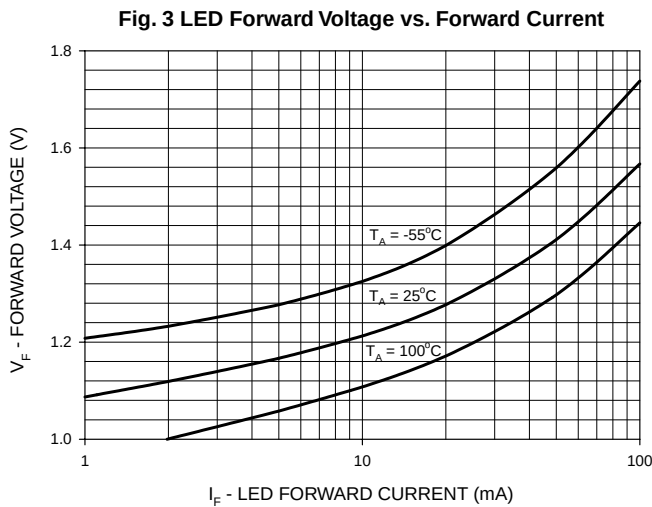


Fig. 3 LED Forward Voltage vs. Forward Current

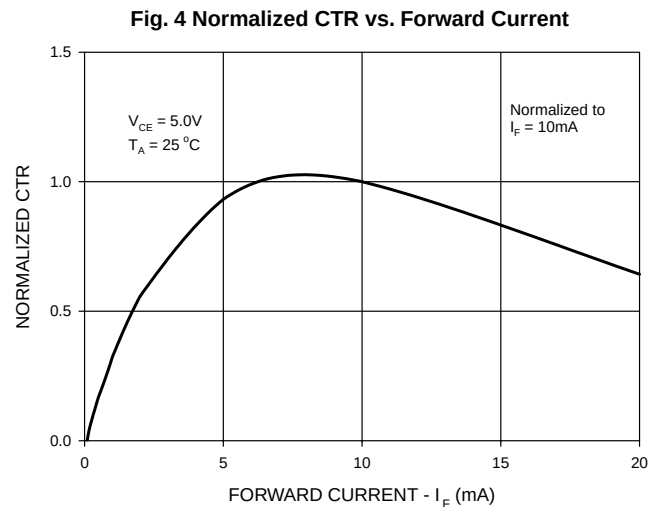


Fig. 4 Normalized CTR vs. Forward Current

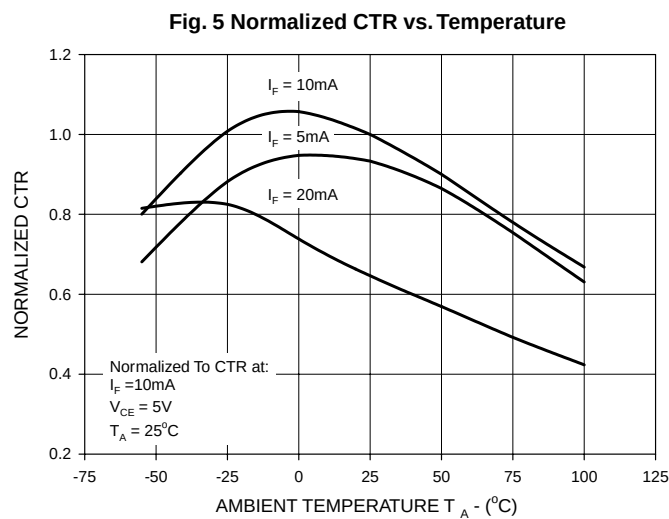


Fig. 5 Normalized CTR vs. Temperature

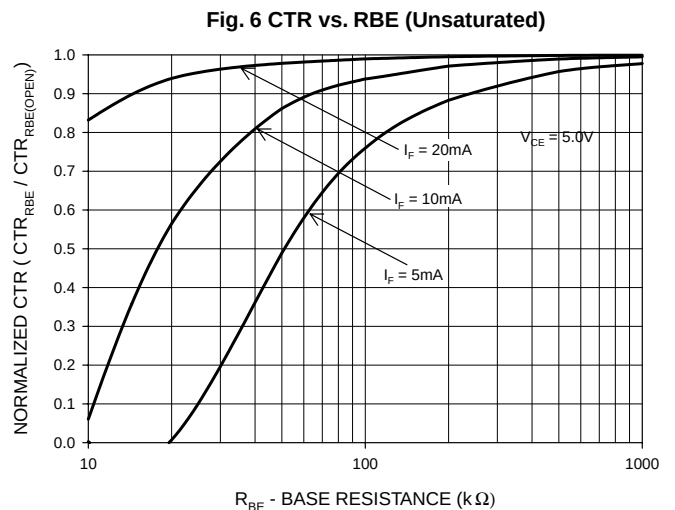


Fig. 6 CTR vs. RBE (Unsaturated)

CNX35U CNX36U CNX38U CNX39U

Fig. 7 CTR vs. R_{BE} (Saturated)

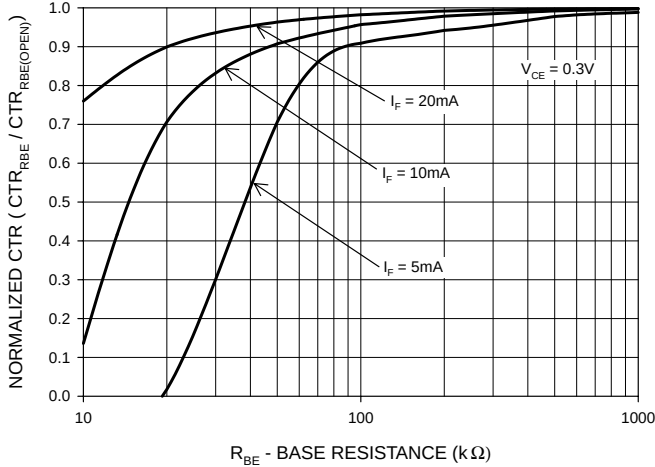


Fig. 8 Normalized t_{on} vs. R_{BE}

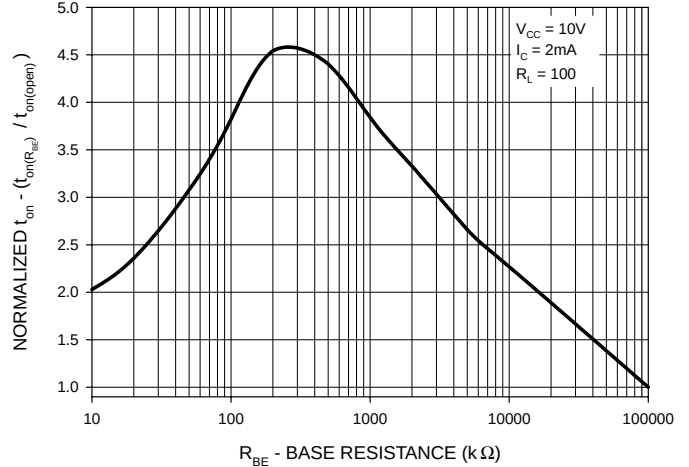


Fig. 9 Normalized t_{off} vs. R_{BE}

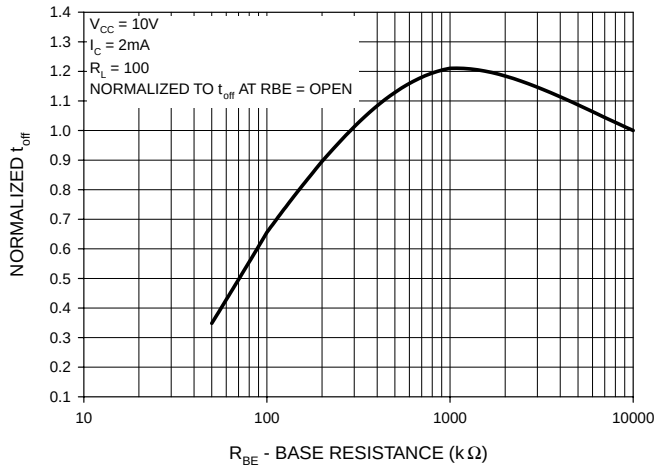


Fig. 10 Switching Speed vs. Load Resistor

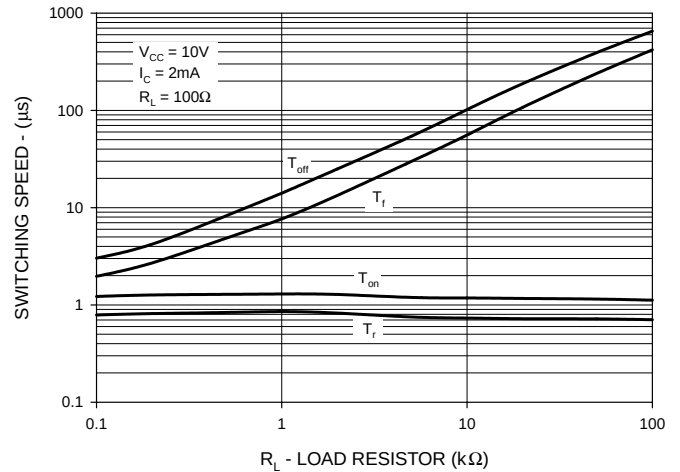
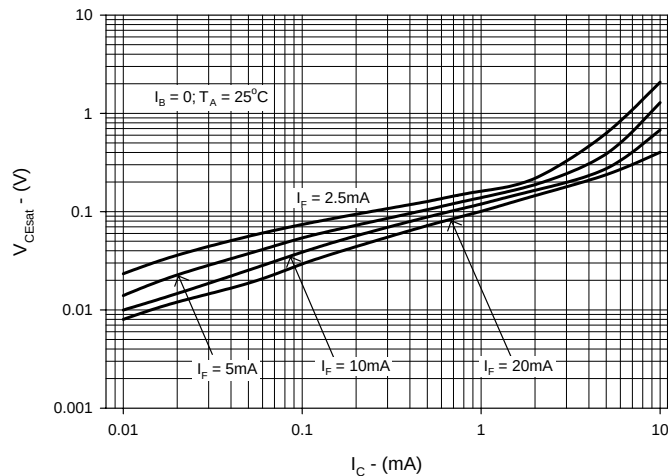
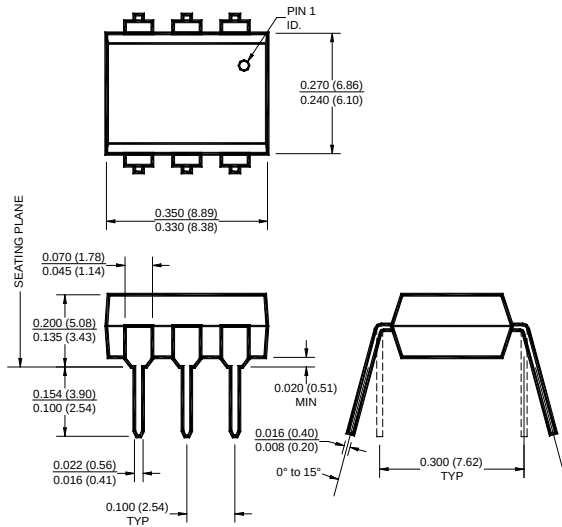


Fig. 11 Collector-Emitter Saturation Voltage as a Function of Collector Current

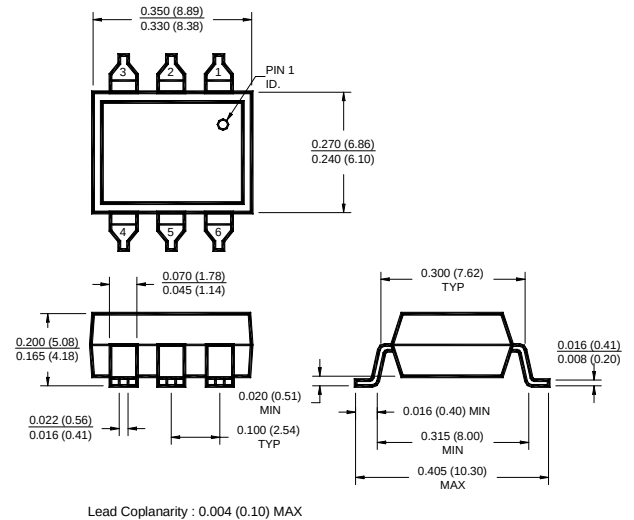


CNX35U CNX36U CNX38U CNX39U

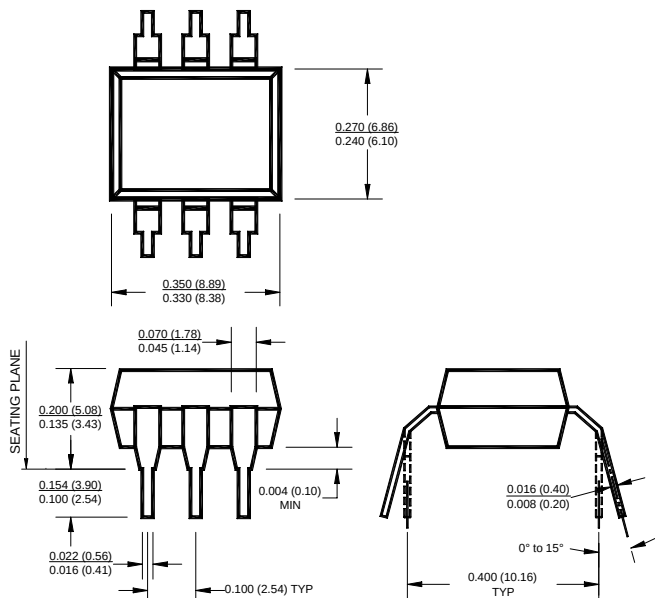
Package Dimensions (Through Hole)



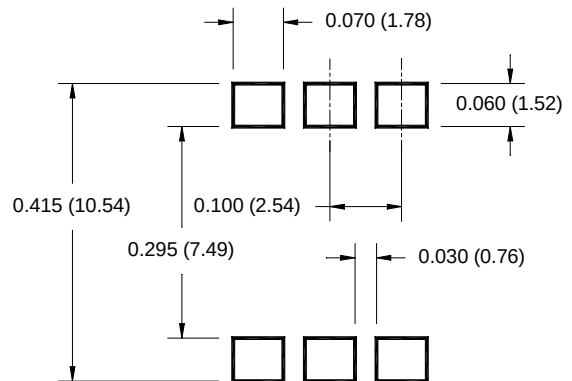
Package Dimensions (Surface Mount)



Package Dimensions (0.4" Lead Spacing)



Recommended Pad Layout for Surface Mount Leadform



NOTE

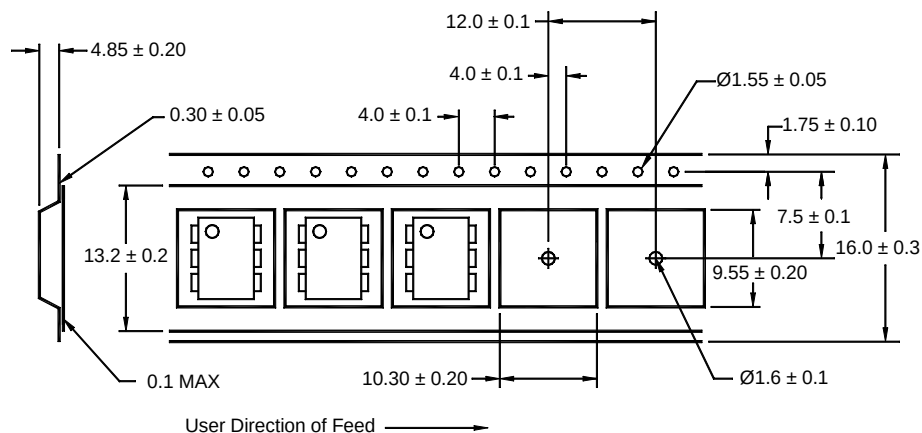
All dimensions are in inches (millimeters)

CNX35U CNX36U CNX38U CNX39U

ORDERING INFORMATION

Option	Order Entry Identifier	Description
S	.S	Surface Mount Lead Bend
SD	.SD	Surface Mount; Tape and reel
W	.W	0.4" Lead Spacing
300	.300	VDE 0884
300W	.300W	VDE 0884, 0.4" Lead Spacing
3S	.3S	VDE 0884, Surface Mount
3SD	.3SD	VDE 0884, Surface Mount, Tape & Reel

Carrier Tape Specifications ("D" Taping Orientation)



NOTE

All dimensions are in inches (millimeters)

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